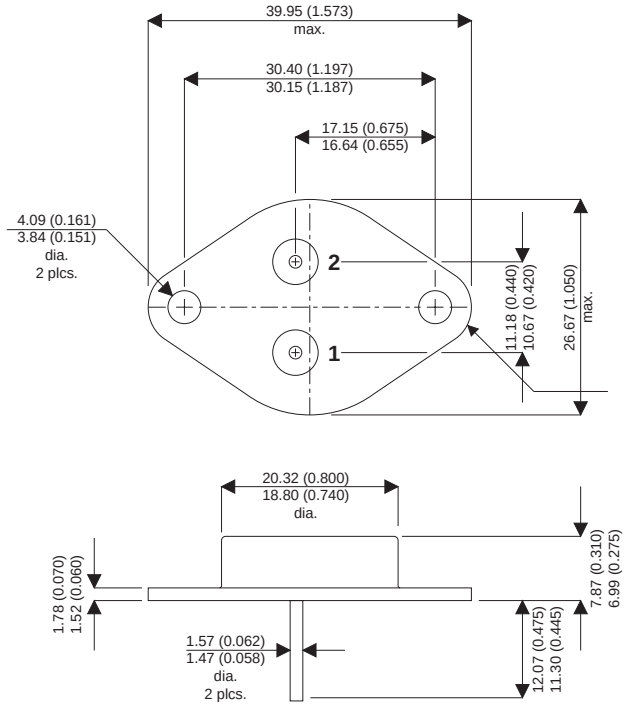
IRF150

MECHANICAL DATA

Dimensions in mm (inches)



TO–3 Metal Package

Pin 1 – Gate Pin 2 – Source Case – Drain

N–CHANNEL POWER MOSFET

V_{DSS}	100V
$I_{D(cont)}$	38A
$R_{DS(on)}$	0.055Ω

FEATURES

- **HERMETICALLY SEALED TO–3 METAL PACKAGE**
- **SIMPLE DRIVE REQUIREMENTS**
- **SCREENING OPTIONS AVAILABLE**

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V_{GS}	Gate – Source Voltage		±20V
I_D	Continuous Drain Current	(V_{GS} = 0 , T_{case} = 25°C)	38A
I_D	Continuous Drain Current	(V_{GS} = 0 , T_{case} = 100°C)	24A
I_{DM}	Pulsed Drain Current [1]		152A
P_D	Power Dissipation @ T_{case} = 25°C		150W
	Linear Derating Factor		1.2W/°C
E_{AS}	Single Pulse Avalanche Energy [2]		150mJ
I_{AR}	Avalanche Current [2]		38A
E_{AR}	Repetitive Avalanche Energy [2]		15mJ
dv/dt	Peak Diode Recovery [3]		5.5V/ns
T_J , T_{stg}	Operating and Storage Temperature Range		-55 to +150°C
T_L	Lead Temperature 1.6mm (0.63”) from case for 10 sec.		300°C

Notes

1) Pulse Test: Pulse Width ≤ 300μs, δ ≤ 2%
2) @ V_{DD} = 50V , L ≥ 160μH , R_G = 25Ω , Peak I_L = 38A , Starting T_J = 25°C
3) @ I_{SD} ≤ 38A , di/dt ≤ 300A/μs , V_{DD} ≤ BV_{DSS} , T_J ≤ 150°C , Suggested R_G = 2.35Ω

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SEME LAB

IRF150

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
	STATIC ELECTRICAL RATINGS					
BV_{DSS}	Drain – Source Breakdown Voltage	V_{GS} = 0 I_D = 1mA	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to 25°C I_D = 1mA		0.13		V/°C
$R_{DS(on)}$	Static Drain – Source On–State Resistance [1]	V_{GS} = 10V I_D = 24A			0.055	Ω
		V_{GS} = 10V I_D = 38A			0.065	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250mA	2		4	V
g_{fs}	Forward Transconductance [1]	V_{DS} ≥ 15V I_{DS} = 24A	9			S (℧)
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0 V_{DS} = 0.8BV_{DSS}			25	μA
		T_J = 125°C			250	
I_{GSS}	Forward Gate – Source Leakage	V_{GS} = 20V			100	nA
I_{GSS}	Reverse Gate – Source Leakage	V_{GS} = –20V			–100	
	DYNAMIC CHARACTERISTICS					
C_{iss}	Input Capacitance	V_{GS} = 0		3700		pF
C_{oss}	Output Capacitance	V_{DS} = 25V		1100		
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		200		
Q_g	Total Gate Charge	V_{GS} = 10V	50		125	nC
Q_{gs}	Gate – Source Charge	I_D = 38A	8		22	
Q_{gd}	Gate – Drain (“Miller”) Charge	V_{DS} = 0.5BV_{DSS}	25		65	
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 50V I_D = 38A R_G = 2.35Ω			35	ns
t_r	Rise Time				190	
$t_{d(off)}$	Turn–Off Delay Time				170	
t_f	Fall Time				130	
	SOURCE – DRAIN DIODE CHARACTERISTICS					
I_S	Continuous Source Current				38	A
I_{SM}	Pulse Source Current [2]				152	
V_{SD}	Diode Forward Voltage [1]	I_S = 38A T_J = 25°C V_{GS} = 0			1.8	V
t_{rr}	Reverse Recovery Time	I_F = 38A T_J = 25°C			500	ns
Q_{rr}	Reverse Recovery Charge [1]	d_i / d_t ≤ 100A/μs V_{DD} ≤ 50V			2.9	μC
t_{on}	Forward Turn–On Time			Negligible		
	PACKAGE CHARACTERISTICS					
L_D	Internal Drain Inductance (measured from 6mm down drain lead to centre of die)			5.0		nH
L_S	Internal Source Inductance (from 6mm down source lead to source bond pad)			13		
	THERMAL CHARACTERISTICS					
$R_{\theta JC}$	Thermal Resistance Junction – Case				0.83	°C/W
$R_{\theta CS}$	Thermal Resistance Case – Sink			0.12		
$R_{\theta JA}$	Thermal Resistance Junction – Ambient				30	

Notes

1) Pulse Test: Pulse Width ≤ 300ms, δ ≤ 2%
2) Repetitive Rating – Pulse width limited by maximum junction temperature.